

OCT. 5.2004 4:14PM

866 751 0075

NO. 1081 P. 9

Form PTO-1449 (Rev. 8-83)		U.S. Department of Com. Patent and Trademark	Attorney Docket: 740756-2646	Sheet 6 of 7 Serial No. 10/642,305			
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		Applicant: Hongyong ZHANG et al. Filing Date: August 18, 2003 Group: 2811 U.S. PATENT DOCUMENTS					
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)	
DHO	4,377,421	03/22/83	Wade et al				
	4,561,906	12/31/85	Calder et al				
	4,619,034	10/28/86	Janning				
	4,651,408	03/24/87	MacElwee et al				
	4,698,486	10/06/87	Sheets				
	4,814,292	03/21/89	Sasaki et al				
	4,847,211	07/11/89	Lee				
	4,882,293	11/21/89	Cembaly et al				
	4,959,700	09/25/90	Yamazaki et al				
	4,998,658	11/06/90	Wright et al				
	4,998,152	03/05/91	Bates et al				
	5,061,642	10/29/91	Fujisaka				
	5,070,379	12/03/91	Nomoto et al				
	5,141,883	08/23/92	Yoshida et al				
	5,198,379	03/30/93	Adan				
	5,208,476	05/04/93	Inoue				
	5,219,786	06/15/93	Noguchi				
	5,278,093	01/11/94	Yonehara				
	5,286,658	02/13/94	Shimakawa et al				
	5,329,140	07/12/94	Sera				
	5,352,291	10/04/94	Zhang et al				
	5,420,048	05/30/95	Kondo				
	5,529,937	06/25/96	Zhang et al				
	5,530,265	06/25/96	Takemura				
	5,696,011	12/09/97	Yamazaki et al				
	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
	G. Kawachi et al., "Large-Area Doping Process for Fabrication of poly-Si Thin Film Transistors Using Bucket Ion Source and XeCl Excimer Laser Annealing", Japanese Journal of Applied Physics, Vol. 29, No. 12, December 1990, pp. L2370-L2372						
	EWJ		Date Considered	11/10/04			

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if no and not considered. Include copy of this form with next communication to applicant.

JB
7/10

NVA274461